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**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Inventors:	<b>Tina J. Wagner et al.</b>	Date:	<b>26 March 2005</b>
Serial No.:	<b>10/605,100</b>	Art Unit:	<b>2818</b>
Filing Date:	<b>09 September 2003</b>	Examiner:	<b>David Vu</b>
Confirmation No.:	<b>2099</b>	Docket No.:	<b>FIS920030249US1</b>
Title:	<b>Method of Manufacture of Raised Source Drain MOSFET with Top Notched Gate Structure Filled with Dielectric Plug In and Device Manufactured Thereby</b>	Attorney:	<b>Graham S. Jones, II 42 Barnard Avenue Poughkeepsie, NY 12603-5023</b>

**AMENDMENT**

**The Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450**

**Your Honor:**

**In response to the Office Action of 1 March 2005, please amend the above-identified application as follows:**

<b>Amendments to the Title</b>	<b>begin on page 2 of this paper.</b>
<b>Amendments to the Abstract</b>	<b>begin on page 3 of this paper</b>
<b>Amendments to the Specification</b>	<b>begin on page 4 of this paper</b>
<b>Amendments to the Claims</b>	<b>begin on page 9 of this paper.</b>
<b>Remarks/Arguments</b>	<b>begin on page 14 of this paper.</b>

**FIS920030249US1**

Serial No.:	10/605,100	Art Unit:	2818
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**IN THE TITLE**

**Please amend the title to read as follows:**

**-- ~~Method of Manufacture of~~ A Raised Source Drain MOSFET with Top Notched Notch Formed on Top of Gate Structure Filled with a Dielectric Plug ~~in and Device Manufactured Thereby~~ --**